

## Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>d, e</sup>	$Q_g$ (Typ.)
- 30	0.016 at $V_{GS} = - 10$ V	- 9.5	15 nC
	0.020 at $V_{GS} = - 4.5$ V	- 8.0	

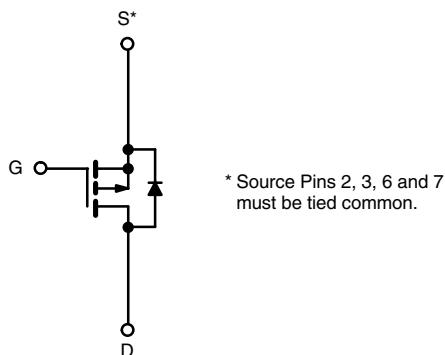
### FEATURES

- Halogen-free
- Trench Power MOSFET
- 100 % UIS Tested


**RoHS**  
 COMPLIANT

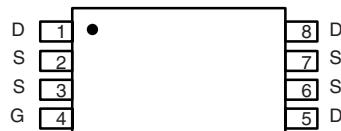
### APPLICATIONS

- Load Switches
  - Notebook PCs
  - Desktop PCs
  - Game Stations



P-Channel MOSFET

TSSOP-8



Top View

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	- 30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$T_C = 25$ °C	$I_D$	A
	$T_C = 70$ °C		
	$T_A = 25$ °C		
	$T_A = 70$ °C		
Pulsed Drain Current	$I_{DM}$	- 32 <sup>e</sup>	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	- 4.1	
	$T_A = 25$ °C	- 2.0 <sup>a, b</sup>	
Avalanche Current	$I_{AS}$	- 20	
Single-Pulse Avalanche Energy	$E_{AS}$	20	
Maximum Power Dissipation	$T_C = 25$ °C	5.0	W
	$T_C = 70$ °C	3.2	
	$T_A = 25$ °C	2.5 <sup>a, b</sup>	
	$T_A = 70$ °C	1.6 <sup>a, b</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, c</sup>	$R_{thJA}$	38	50	°C/W
Maximum Junction-to-Foot	$R_{thJF}$	20	25	

## Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b.  $t = 10$  s.
- c. Maximum under Steady State conditions is 85 °C/W.
- d. Based on  $T_C = 25$  °C.
- e. Limited by package.

**SPECIFICATIONS**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

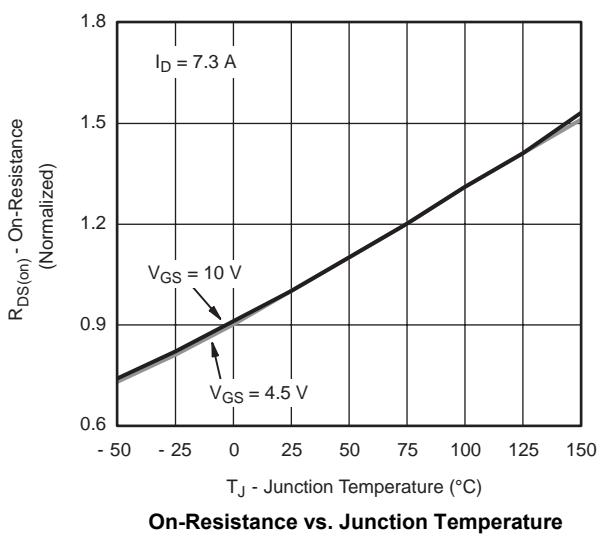
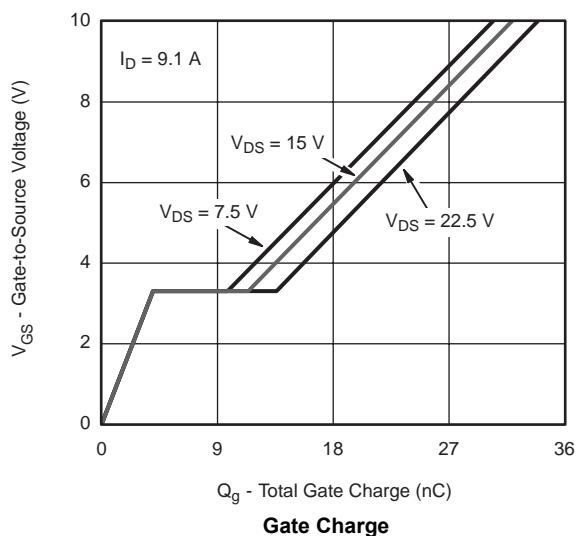
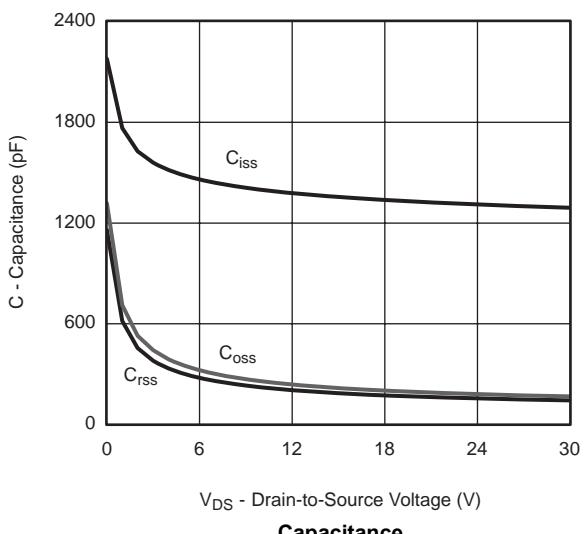
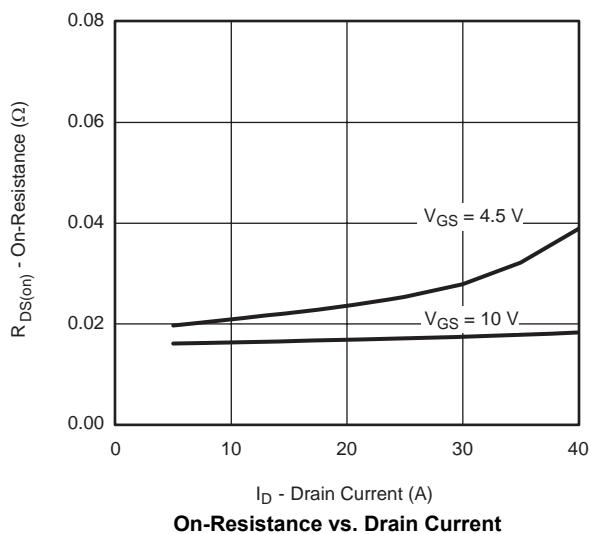
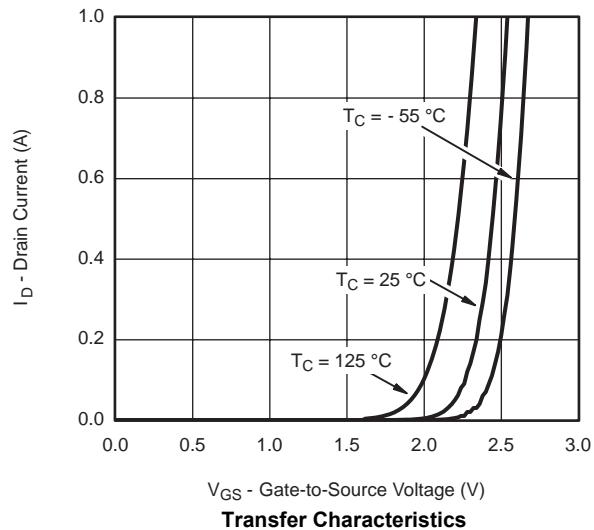
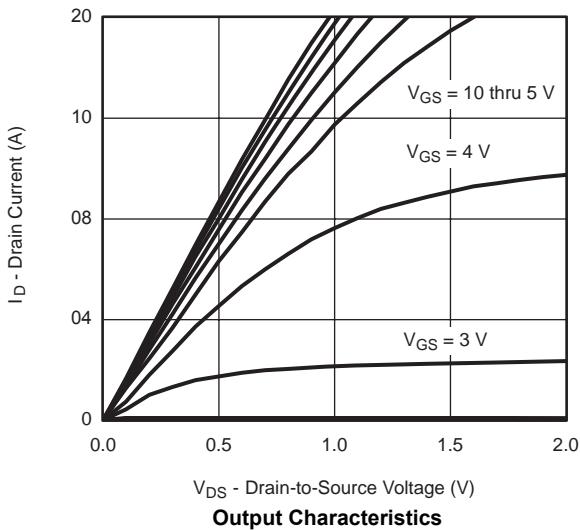
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = -250 \mu\text{A}$	-30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$		-31		mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			4.5		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = -250 \mu\text{A}$	-1.0		-3.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30 \text{ V}$ , $V_{GS} = 0 \text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -30 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$			-5	
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq -10 \text{ V}$ , $V_{GS} = -10 \text{ V}$	-30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = -10 \text{ V}$ , $I_D = -7.3 \text{ A}$		0.016		$\Omega$
		$V_{GS} = -4.5 \text{ V}$ , $I_D = -6.2 \text{ A}$		0.020		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10 \text{ V}$ , $I_D = -9.1 \text{ A}$		23		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		1350		pF
Output Capacitance	$C_{oss}$			215		
Reverse Transfer Capacitance	$C_{rss}$			185		
Total Gate Charge	$Q_g$	$V_{DS} = -15 \text{ V}$ , $V_{GS} = -10 \text{ V}$ , $I_D = -9.1 \text{ A}$		32	50	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}$ , $V_{GS} = -4.5 \text{ V}$ , $I_D = -9.1 \text{ A}$		15	25	
Gate-Drain Charge	$Q_{gd}$			4		
Gate Resistance	$R_g$			7.5		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -15 \text{ V}$ , $R_L = 15 \Omega$ $I_D \geq -1 \text{ A}$ , $V_{GEN} = -10 \text{ V}$ , $R_g = 1 \Omega$		5.8		$\Omega$
Rise Time	$t_r$			10	15	
Turn-Off Delay Time	$t_{d(\text{off})}$			8	15	
Fall Time	$t_f$			45	70	
Turn-On Delay Time	$t_{d(\text{on})}$			12	25	
Rise Time	$t_r$			42	70	
Turn-Off Delay Time	$t_{d(\text{off})}$			35	60	
Fall Time	$t_f$			40	70	
				16	30	
<b>Drain-Source Body Diode Characteristics</b>						
Continous Source-Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$			-4.1	A
Pulse Diode Forward Current	$I_{SM}$				-32	
Body Diode Voltage	$V_{SD}$	$I_S = -2 \text{ A}$ , $V_{GS} = 0 \text{ V}$		-0.75	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -2 \text{ A}$ , $dl/dt = 100 \text{ A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$		34	60	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			22	40	
Reverse Recovery Fall Time	$t_a$			11		ns
Reverse Recovery Rise Time	$t_b$			23		

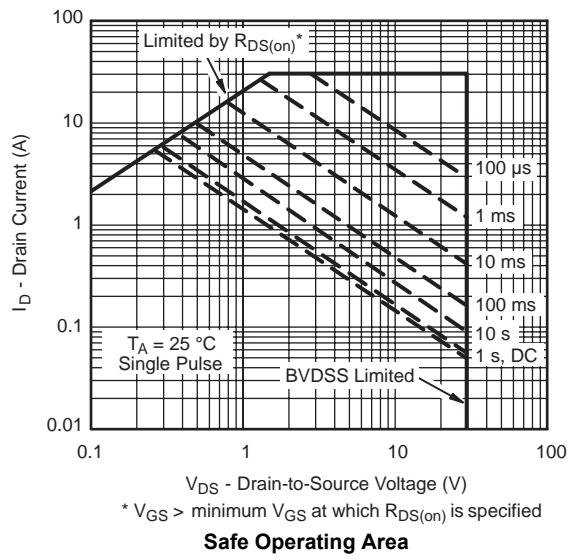
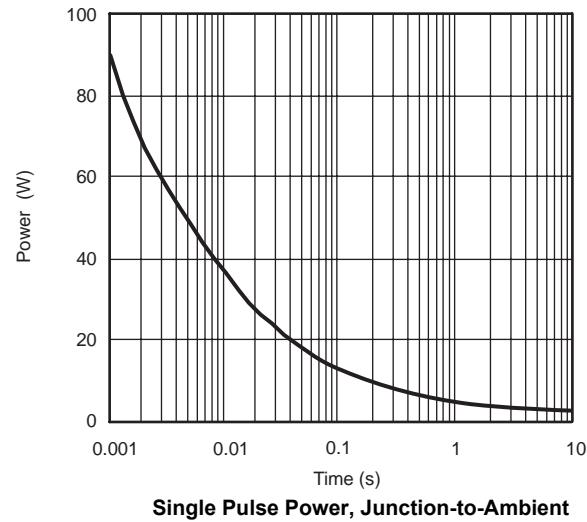
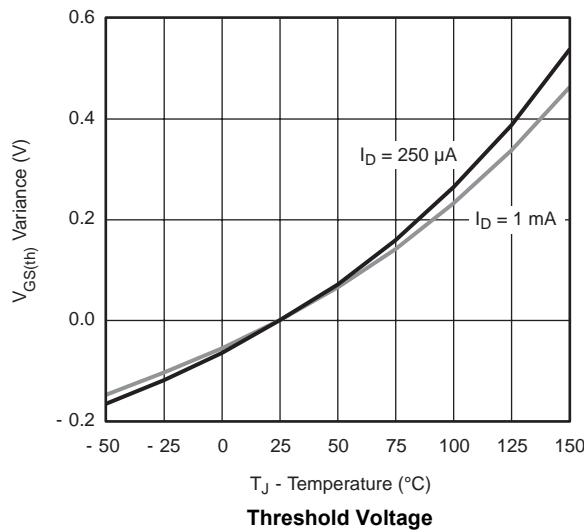
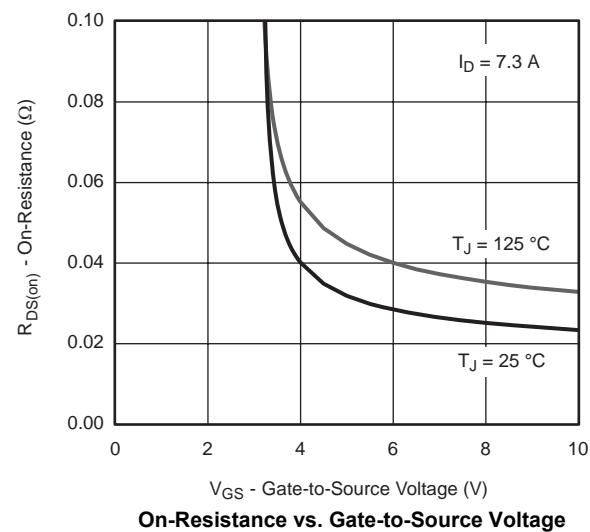
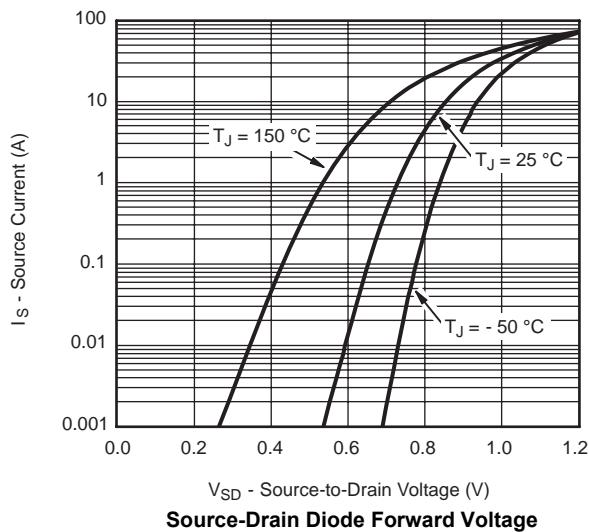
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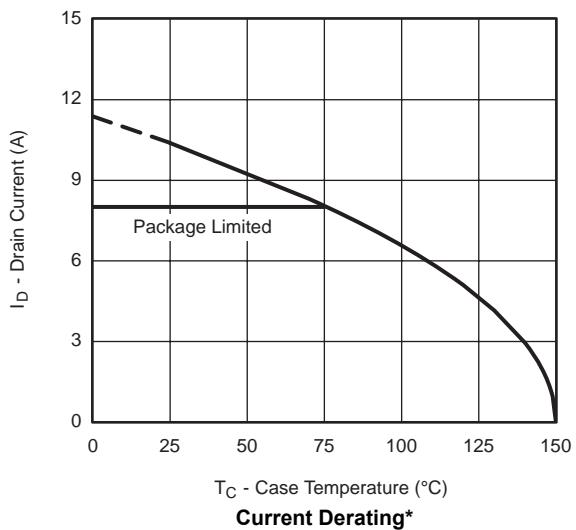
a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

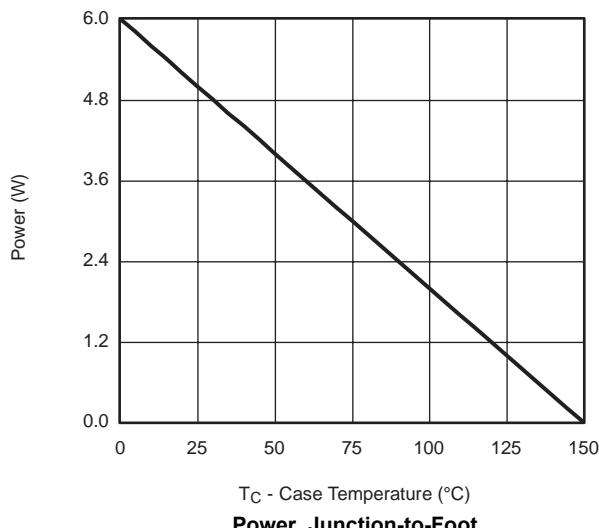
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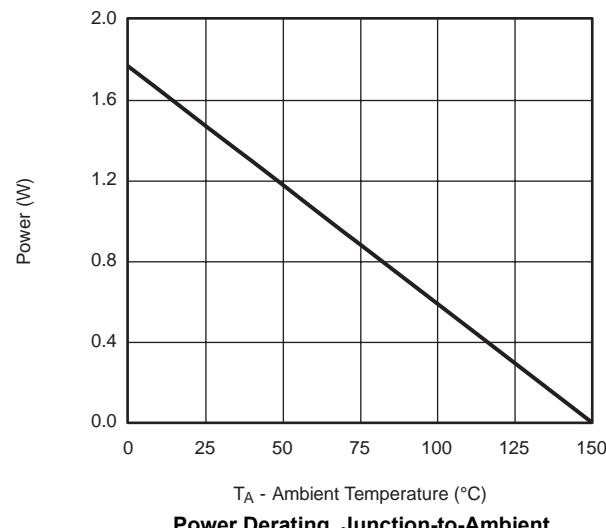
TC - Case Temperature (°C)

Current Derating\*



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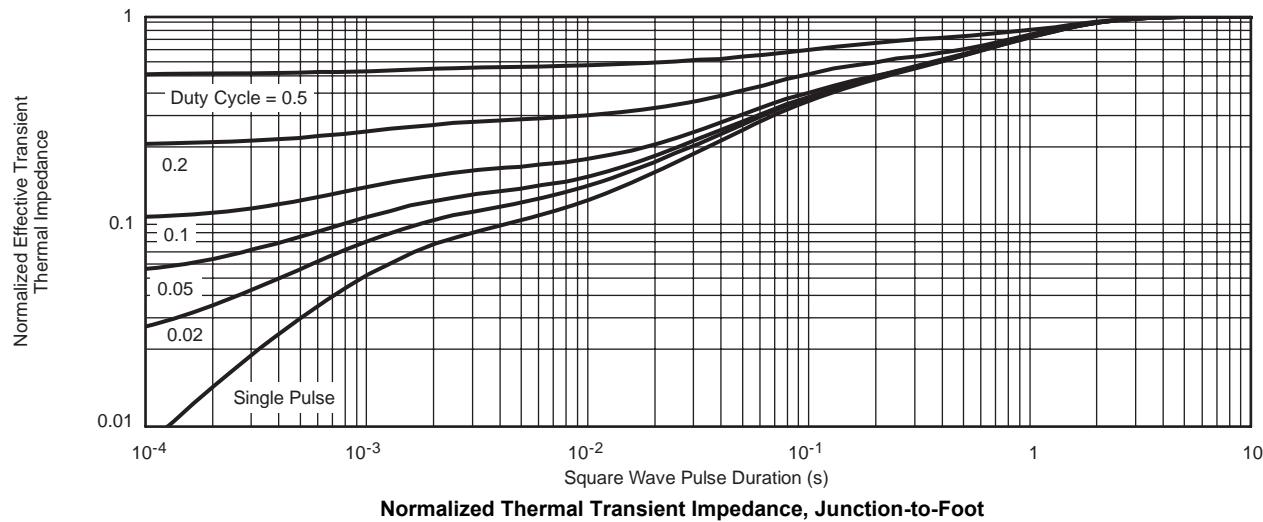
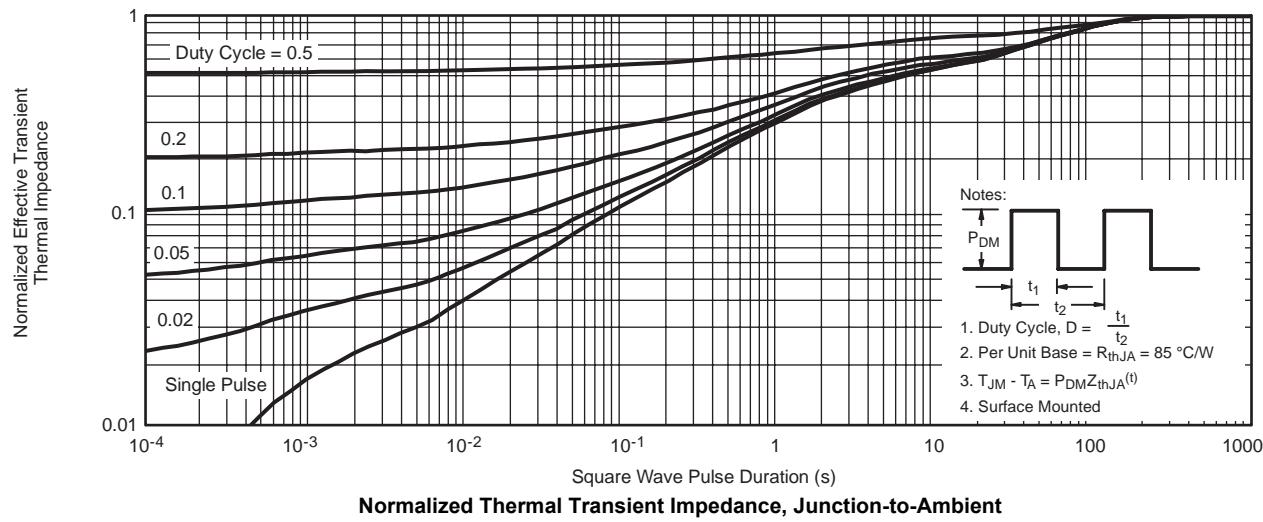
Power, Junction-to-Foot



TA - Ambient Temperature (°C)

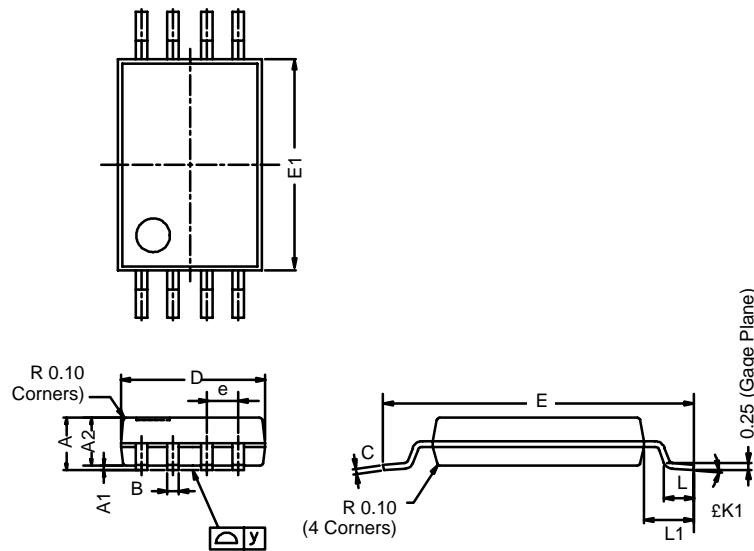
Power Derating, Junction-to-Ambient

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


**TSSOP: 8-LEAD**

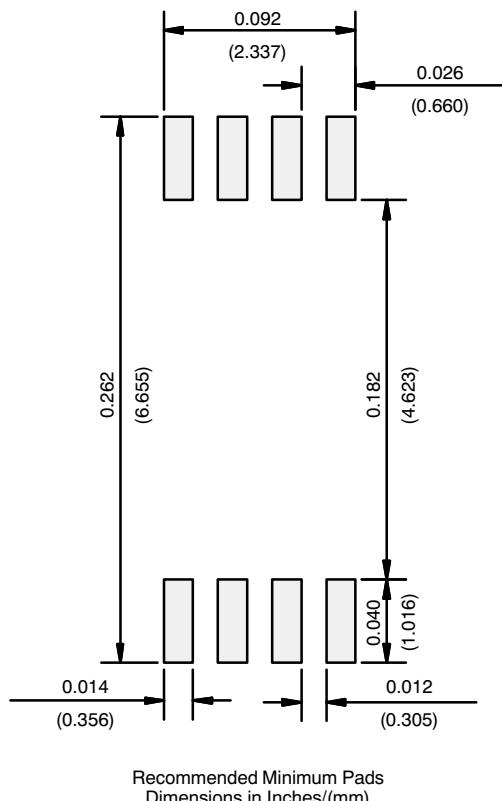
JEDEC Part Number: MO-153



Dim	MILLIMETERS		
	Min	Nom	Max
<b>A</b>	—	—	1.20
<b>A<sub>1</sub></b>	0.05	0.10	0.15
<b>A<sub>2</sub></b>	0.80	1.00	1.05
<b>B</b>	0.19	0.28	0.30
<b>C</b>	—	0.127	—
<b>D</b>	2.90	3.00	3.10
<b>E</b>	6.20	6.40	6.60
<b>E<sub>1</sub></b>	4.30	4.40	4.50
<b>e</b>	—	0.65	—
<b>L</b>	0.45	0.60	0.75
<b>L<sub>1</sub></b>	0.90	1.00	1.10
<b>Y</b>	—	—	0.10
<b>£K1</b>	0°	3°	6°

ECN: S-03946—Rev. G, 09-Jul-01  
 DWG: 5844

## RECOMMENDED MINIMUM PADS FOR TSSOP-8



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